

FIG.1A

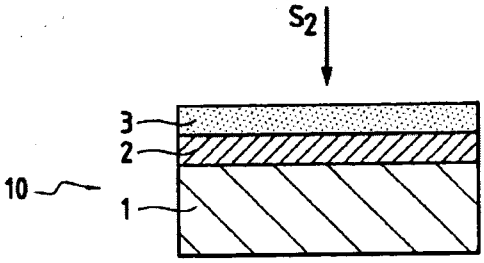


FIG.1B

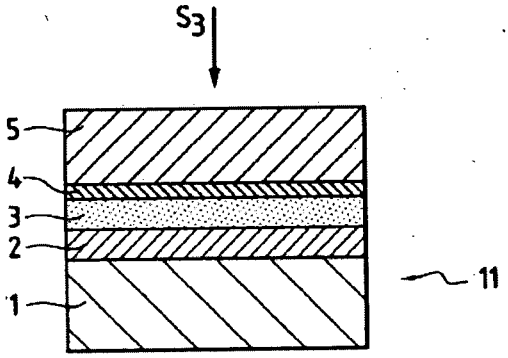


FIG.1C

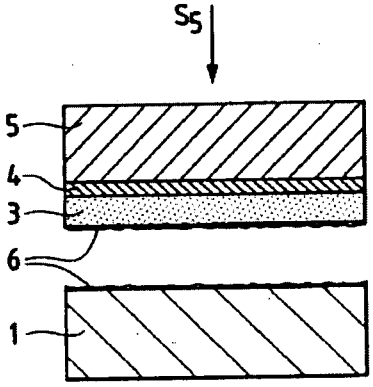


FIG.1D

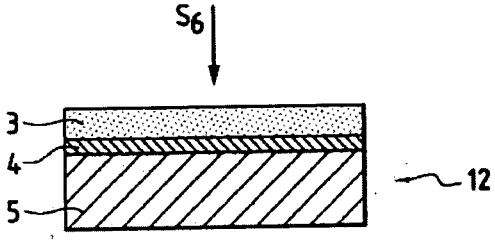


FIG.1E

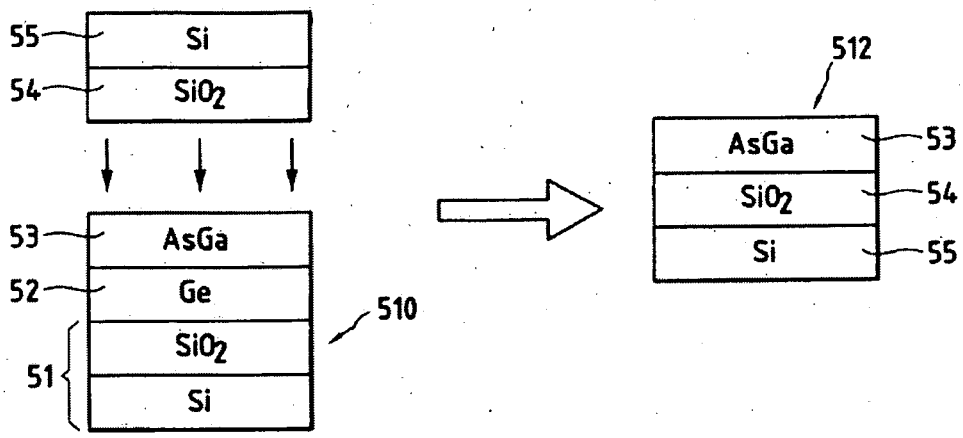

55
Si
54
SiO2
53
AsGa
52
Ge
51
SiO2
Si
510
512
AsGa
53
SiO2
54
Si
55

FIG.5

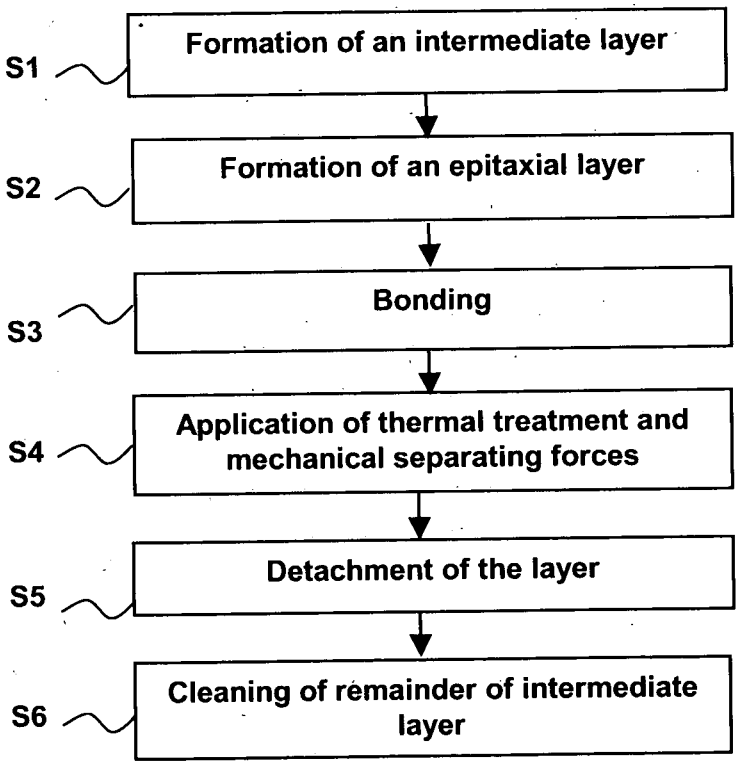

S1
Formation of an intermediate layer
S2
Formation of an epitaxial layer
S3
Bonding
S4
Application of thermal treatment and mechanical separating forces
S5
Detachment of the layer
S6
Cleaning of remainder of intermediate layer

FIG.2

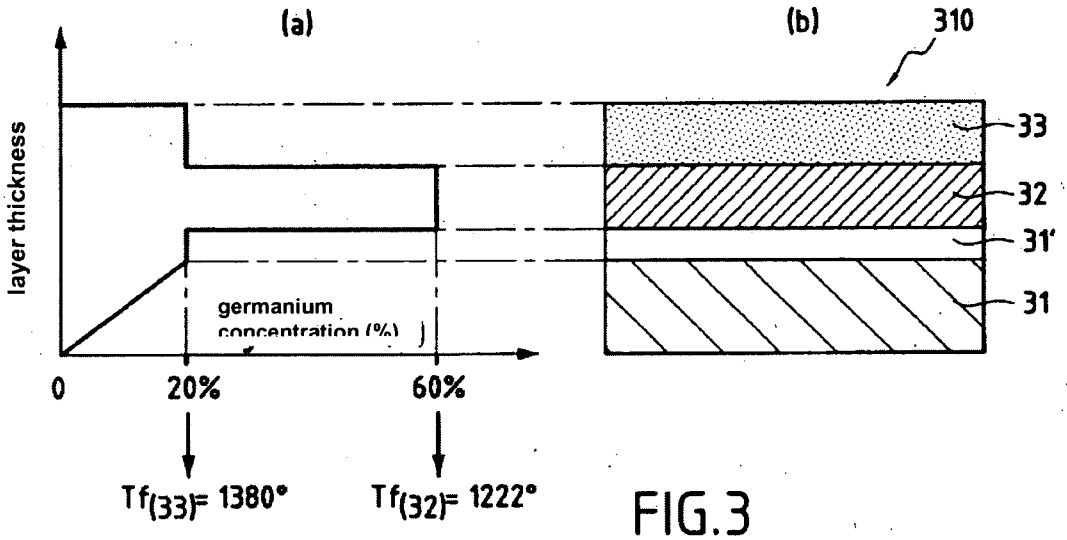

(a)
(b)
310
layer thickness
33
32
31'
31
germanium
concentration (%)
0
20%
60%
Tf(33)= 1380°
Tf(32)= 1222°

FIG.3

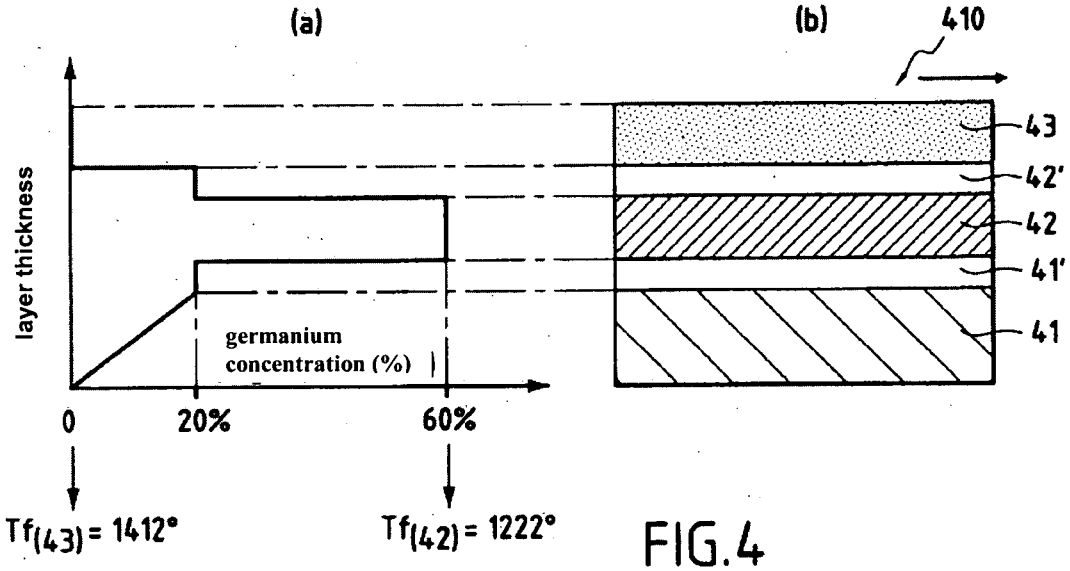

(a)
(b)
410
layer thickness
43
42'
42
41'
41
germanium
concentration (%)
0
20%
60%
Tf(43) = 1412°
Tf(42) = 1222°

FIG.4

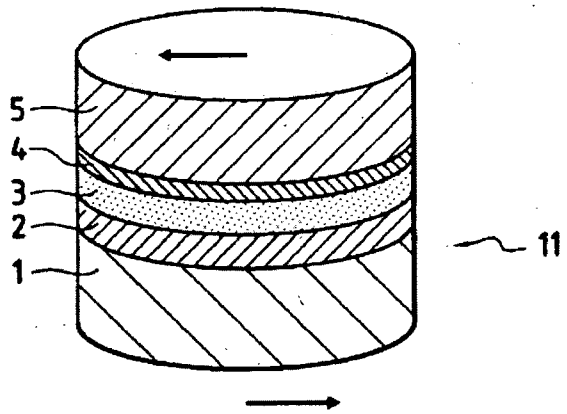


FIG.6A

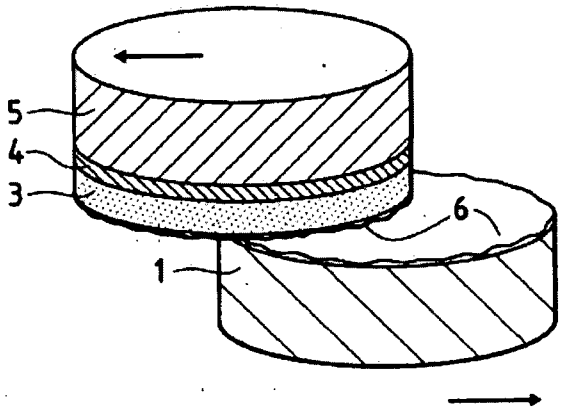


FIG.6B